

UTC UNISONIC TECHNOLOGIES CO., LTD

BSS84Z

Preliminary

0.13A, 50V P-CHANNEL ENHANCEMENT MODE FIELD **EFFECT TRANSISTOR**

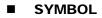
DESCRIPTION

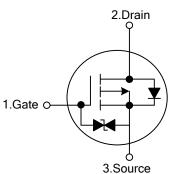
These P-Channel enhancement mode field vertical D-MOS transistors are in a SOT-23-3 SMD package, and in most applications they require up to 0.13A DC and can deliver current up to 0.52A.

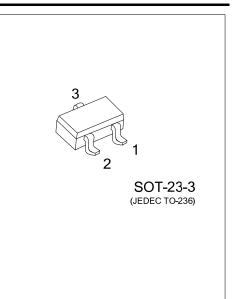
This product is particularly suited to low voltage applications requiring a low current high side switch.

FEATURES

* R_{DS(ON)}=10Ω @ V_{GS}=-5V



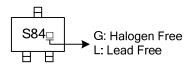




ORDERING INFORMATION

Ordering Number		Daakaga	Pin Assignment			Booking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BSS84ZL-AE2-R	BSS84ZG-AE2-R	SOT-23-3	S	G	D	Tape Reel	
Note: Pin Assignment: G: Gate D: Drain S: Source							
BSS84ZL-AE2-R		(1) R: Tape Reel (2) AE2: SOT-23 (3) G: Halogen F	-3	.ead Fre	æ		

MARKING



■ **ABSOLUTE MAXIMUM RATINGS** (T_A = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V _{DSS}	-50	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Continuous Drain Current	DC		-0.13	•	
	Pulse	ID	-0.52	A	
Power Dissipation		PD	0.36	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	350	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, Ι _D =-250μΑ	-50			V		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-50V, V _{GS} =0V			-15	μA		
Gate-Body Leakage, Forward	I _{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			±10	μA		
ON CHARACTERISTICS (Note)								
Gate-Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-1m A		-1.7	-2	V		
Statia Drain, Source On, Desistance	R _{DS(ON)}	V _{GS} =-5V, I _D =-0.1A		1.2	10	Ω		
Static Drain–Source On–Resistance		V _{GS} =-55 V, I _D =-0.1A, T _J =125℃		1.9	17	Ω		
On-State Drain Current	I _{D(ON)}	V _{GS} =-10 V, V _{DS} =-5V				А		
Forward Transconductance	g _{FS}	V _{DS} =-25V, I _D =-0.1A		0.6		S		
DYNAMIC PARAMETERS								
Input Capacitance	C _{ISS}	V _{DS} =-25V, V _{GS} =0V, f=1MHz		73		pF		
Output Capacitance	C _{oss}			10		рF		
Reverse Transfer Capacitance	C _{RSS}			5		pF		
SWITCHING PARAMETERS (Note)				_				
Total Gate Charge	Q _G	V 20V/ V 40V/		0.9	1.3	nC		
Gate Source Charge	Q _{GS}	V _{DS} =-30V, V _{GS} =-10V, -I _D =-0.1A		0.2		nC		
Gate Drain Charge	Q _{GD}			0.3		nC		
Turn-ON Delay Time	t _{D(ON)}			2.5	5	ns		
Turn-ON Rise Time	t _R	V_{DD} =-30V, I _D =-0.1A,V _{GS} =-10V, R _G =6Ω,		6.3	13	ns		
Turn-OFF Delay Time	t _{D(OFF)}			10	20	ns		
Turn-OFF Fall-Time	t _F			4.8	9.6	ns		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S =-0.26A (Note)		-0.8	-1.2	V		
Max. Diode Forward Current	ls				-0.13	А		
Nata: Dulas tast mulas width < 000ms duty a	1 4 00/							

Note: Pulse test, pulse width ≤ 300us, duty cycle≤ 2%



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